

In th Claims

A marked up version showing amendments to any claims being changed is provided in one or more accompanying pages separate from this amendment in accordance with 37 C.F.R. § 1.121(c)(1)(ii). Any claim not accompanied by a marked up version has not been changed relative to the immediate prior version, except that marked up versions are not being supplied for any canceled claim.

Cancel claims ~~1-36~~<sup>38-36</sup> and 39-42.

Please add claims 43-45 as follows:

43. (New) The method of claim 37 wherein the forming a fluorine containing layer comprises forming a sacrificial fluorine containing layer over the thin film transistor layer by chemical vapor deposition utilizing  $WF_6$  and  $SiH_4$  precursors.

44. (New) The method of claim 43 further comprising, after the transferring fluorine, removing the sacrificial layer from over the thin film transistor layer.

45. (New) A method of forming a bottom-gated thin film transistor comprising the following steps:

forming a transistor gate;

forming a polycrystalline thin film transistor layer over the transistor gate;

forming a fluorine containing layer over the polycrystalline thin film transistor layer;

providing a buffering layer intermediate the thin film transistor layer and the fluorine containing layer; and

transferring fluorine into the polycrystalline thin film transistor layer from the fluorine containing layer.

**REMARKS**